

ABSTRACT

A semiconductor device including high-integrated memory cells and a method for fabricating the semiconductor device is provided.

- 5 The method includes forming a first vertical stack in which first semiconductor layers are vertically stacked over a substrate, etching the first semiconductor layers of the first vertical stack and forming first contact holes, forming dummy semiconductor layers from an uppermost first semiconductor layer of the first vertical stack, forming
- 10 second semiconductor layers on the dummy semiconductor layers to form a second vertical stack, etching the second semiconductor layers of the second vertical stack and forming second contact holes, and replacing the first and second semiconductor layers with pads.

15 FIG. 15